

ZX5T951GQ

60V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.112 grams (Approximate)

Features

- BV_{CEO} > -60V
- I_C = -5.5A High Continuous Collector Current
- I_{CM} = -15A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -70mV @ -1A
- R_{SAT} = 39mΩ for a Low Equivalent On-Resistance
- h_{FE} Specified Up to -10A for a High Gain Hold Up
- Complementary NPN Type: ZX5T851GQ
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The ZX5T951GQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

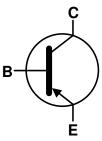
https://www.diodes.com/quality/product-definitions/

Applications

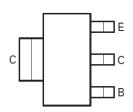
- DC-DC Converters
- MOSFET & IGBT Gate Drivers
- Charging Circuits
- Power Switches
- Motor Control







Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

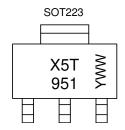
Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZX5T951GQTC	X5T951	13	12	4000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



X5T 951 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 0= 2020) WW or $\overline{W}W$ = Week Code (01~53)

Absolute Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-5.5	Α
Peak Pulse Current	I _{CM}	-15	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)		3.0 24	W
Linear Derating Factor	(Note 6)	P _D	1.6 12.8	mW /°C
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	42	
Thermal nesistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	78	°C/W
Thermal Resistance Junction to Lead (No		$R_{ heta JL}$	10.48	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	٧	С

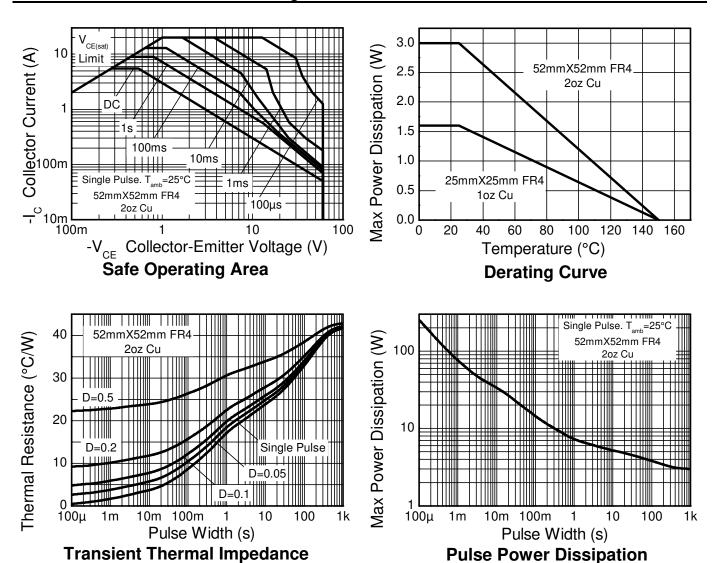
Notes: 5. For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Same as Note 5 except the device is surface mounted on 25mm x 25mm with 1oz copper. 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





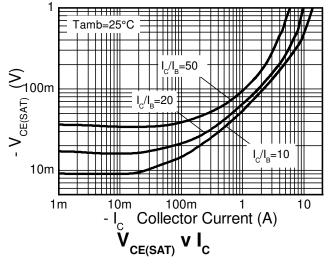
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

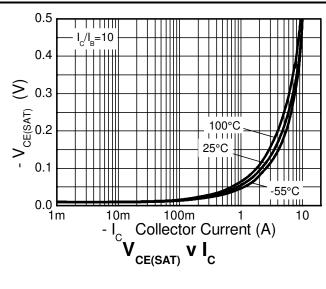
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	-100	-120	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	-100	-120	_	V	$I_C = -1\mu A$, RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-60	-80	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	_	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	Ісво	_	<-1 —	-20 -0.5	nA μA	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Collector-Emitter Cutoff Current	l _{CER} R ≤ 1kΩ	_	<-1 —	-20 -0.5	nA μA	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Emitter Cutoff Current	I _{EBO}	_	<-1	-10	nA	V _{EB} = -6V
		100	250	_	_	$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
Static Forward Current Transfer Ratio (Note 9))) h _{FE}	100	200	300		$I_C = -2A$, $V_{CE} = -1V$
Static Forward Current Transfer Hatto (Note 9)		45	90	_		$I_C = -5A$, $V_{CE} = -1V$
		10	25	_		I _C = -10A, V _{CE} = -1V
	V _{CE(sat)}	_	-15	-25	mV	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		_	-55	-70		$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 9)		_	-90	-120		$I_C = -2A$, $I_B = -200mA$
		_	-195	-250		$I_C = -5A$, $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	_	-1030	-1150	mV	$I_C = -5A$, $I_B = -500$ mV
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	_	-920	-1020	mV	$I_C = -5A$, $V_{CE} = -1V$
Output Capacitance (Note 9)	C _{obo}	_	48	_	pF	$V_{CB} = -10V$, $f = 1MHz$
Transition Frequency	f _T	_	120	_	MHz	V _{CE} = -10V, I _C = -100mA f = 50MHz
Switching Time	t _{on}	_	39	_	ns	$V_{CC} = -10V, I_{C} = -1A$
Ownerming Time	t _{off}	_	370	_	115	$I_{B1} = -I_{B2} = -100 \text{mA}$

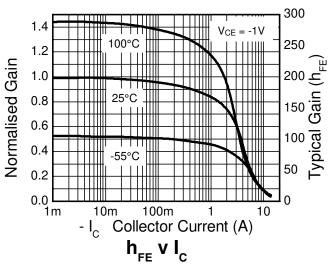
Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

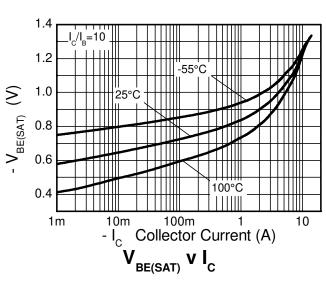


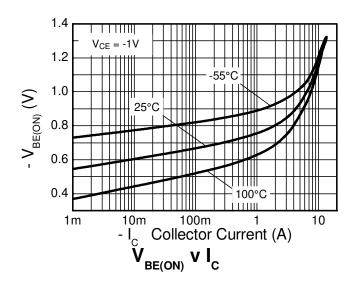
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)









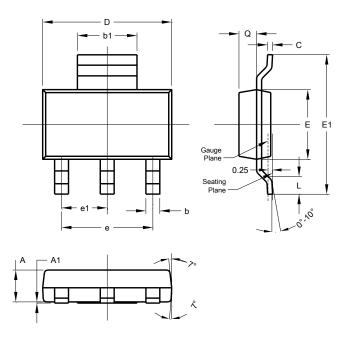


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Package Outline Dimensions

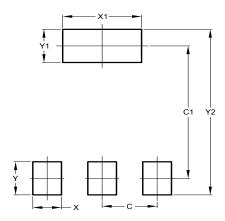
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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